

HiPerFET™ Power MOSFETs

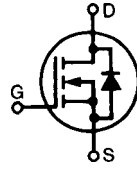
**IXFH 26N60/IXFT 26N60
IXFK 28N60**

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}

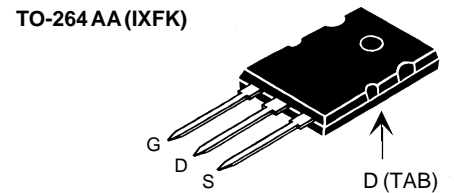
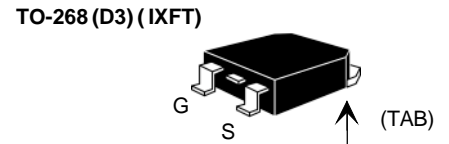
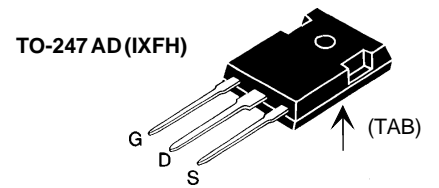
V_{DSS}	I_{D25}	$R_{DS(on)}$
600 V	26 A	0.25 Ω
600 V	28 A	0.25 Ω

$t_{rr} \leq 250 \text{ ns}$

Preliminary data



Symbol	Test Conditions	Maximum Ratings		
		IXFH/ IXFT	IXFK	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	600	600	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	600	600	V
V_{GS}	Continuous	± 20	± 20	V
V_{GSM}	Transient	± 30	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$, Chip capability	26	28	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	104	112	A
I_{AR}	$T_C = 25^\circ\text{C}$	26	28	A
E_{AR}	$T_C = 25^\circ\text{C}$	50	50	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	1.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	5	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	360	416	W
T_J		-55 ... +150		$^\circ\text{C}$
T_{JM}			150	$^\circ\text{C}$
T_{stg}		-55 ... +150		$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	0.9/6	Nm/lb.in.
Weight		6	10	g



G = Gate
S = Source TAB = Drain
Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$	2		4.5 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$			25 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			0.25 Ω

Features

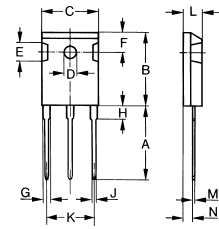
- International standard packages
- Epoxy meet UL94V-0, flammability classification
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Avalanche energy and current rated
- Fast intrinsic Rectifier

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	11	18	S	
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		5000	pF	
C_{oss}			600	pF	
C_{rss}			250	pF	
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1.5\ \Omega$ (External),		30	ns	
t_r			43	ns	
$t_{d(off)}$			110	ns	
t_f			30	ns	
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		250	300	nC
Q_{gs}			33	45	nC
Q_{gd}			115	150	nC
R_{thJC}		26N60 28N60		0.35 0.30	K/W
R_{thCK}	TO-247 TO-264		0.25 0.15		K/W

TO-247 AD (IXFH) Outline



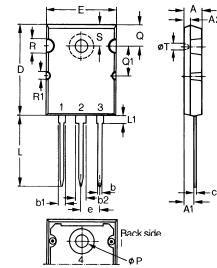
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

Source-Drain Diode

Characteristic Values
($T_J = 25^\circ\text{C}$, unless otherwise specified)

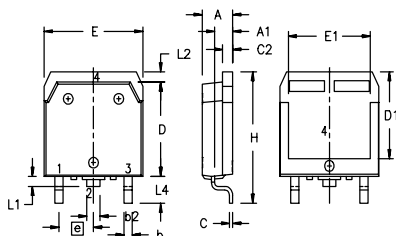
Symbol	Test Conditions	Characteristic Values			
		min.	typ.	max.	
I_S	$V_{GS} = 0\text{ V}$	26N60 28N60		26 28	A A
I_{SM}	Repetitive; pulse width limited by T_{JM}	26N60 28N60		104 112	A A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5	V
t_{rr}	$I_F = I_S - di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250	ns
Q_{RM}			1		μC
I_{RM}			10		A

TO-264 AA (IXFK) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

TO-268AA (D³ PAK)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A1	2.7	2.9	.106	.114
A2	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b2	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E1	13.3	13.6	.524	.535
e	5.45 BSC		.215 BSC	
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3	0.25 BSC		.010 BSC	
L4	3.80	4.10	.150	.161

Min. Recommended Footprint

